

## **Quarterly Reliability Monitoring Results**

## Quarters: Q1/2022 to Q4/2023

Based on structural similarity

Supplier Nexperia B.V.		User Part Number						
		PDTA114ET-Q						
Name of Laboratory  Assembly reliability labs  Based on AEC-Q101 Test		Part Description						
		Nexperia DHAM Small Signal Bipolar Transistor						
		SMD package						
		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
	TEST							
	Pre- and Post-Stress							
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113						
		Bake Tamb = 125 °C	24 hours					
	PC	Soak Tamb = 85 °C, RH = 85%	168 hours					
# A1	Preconditioning	Reflow soldering	3 cycles	1674	70490	0		
		MIL-STD-750-1						
	HTRB	M1039 Method A						
	High Temperature Reverse Bias	Tj = Tjmax, Vr = 100% of max. datasheet				_		
# B1	Bias	reverse voltage	1000 hours	415	18680	0		
		JECD22 A104						
<b>"</b> • • •	TC Temperature Cycling	JESD22-A104 -65 °C to Tjmax, not to exceed 150°C	1000	242	15260	0		
# A4	remperature Cycling	-03 C to Tjillax, flot to exceed 130 C	1000 cycles	343	15360	0		
	UHAST	JESD22-A118						
# A3 <b>or</b>	Unbiased HAST	Tamb = 130 °C, RH = 85 %	— 96 hours	362	15920	0		
	0.10.0000 1.7.001	JESD22-A102						
	AC	Tamb = 121 °C, RH = 100 %						
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)						
7 713 dic		,						
	H3TRB	JESD22-A101						
	High Humidity High	Tamb = 85 °C, RH = 85%, VR = 80 % of						
# A2 alt		rated reverse voltage <sup>[1]</sup>	1000 hours	343	15360	0		
		MIL-STD-750 Method 1037						
	IOL	ton = toff, devices powered to insure $\Delta Tj$ =						
# A5	Intermittent Operating Life		1000 hours	343	15360	0		
	RSH	JESD22-A111						
# C8	Resistance to Solder Heat	260 °C ± 5 °C	10 s	283	8490	0		
	SD							
# C10	Solderability	J-STD-002		214	6420	0		

<sup>[1]</sup> The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

## Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	18680	0	0,23	4,40E+09

<sup>© 2024</sup> Nexperia B.V.

All information hereunder is per Nexperia's best knowledge. This document does not provide for any representation or warranty express or implied by Nexperia. In case Nexperia has tested the product, this documentation reflects the outcome of the analysis of the actually tested parts only.

nexperia.com